

ABSTRACT

A high-frequency power module as a component of a radio communication system capable of performing communications in two frequency bands such as GSM and DCS includes: a first transistor for output detection for receiving a signal which is the same as an input signal of a first power amplification transistor for amplifying a high frequency signal on the GSM side and a first current mirror circuit for passing current proportional to current of the transistor; and a second transistor for output detection for receiving an input signal of a second power amplification transistor for amplifying a high frequency signal on the DCS side and a second current mirror circuit for passing current proportional to current of the transistor. A sense resistor for converting current on the transfer side of the current mirror circuits to voltage, using the voltage as an output level detection signal, comparing the detected output level with a required output level, accordingly controlling the output level, and converting current transferred from the first and second current mirror circuits to voltage is shared by the GSM and DCS.